

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

M4065.069/PC

Application Number

Applicant(s)

Garo J. Derderian

Filing Date

Concurrently Filed Herewith

Group Art Unit

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TAM	A	5,696,384	12/1997	OGI et al.	252	182.12	
TAM	B	5,751,019	05/1998	FAIR	257	68	
TAM	C	5,214,302	05/1993	UCHIDA et al.	257	370	
TAM	D	5,320,978	06/1994	HSU	437	192	
TAM	E	5,494,704	02/1996	ACKERMAN	427	237	
TAM	F	5,572,052	11/1996	KASHIHARA et al.	257	295	
TAM	G	5,381,302	01/1995	SANDHU et al.	361	305	
TAM	H	5,506,166	04/1996	SANDHU et al.	437	60	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TAM	1	KWON, J. et al., CHARACTERIZATION OF P ₁ THIN FILMS DEPOSITED BY METALLORGANIC CHEMICAL VAPOR DEPOSITION FOR FERROELECTRIC BOTTOM ELECTRODES, J. Electrochem. Soc., Vol. 144, No. 8, August 1997, pps. 2848-2854.

EXAMINER

DATE CONSIDERED

4/14/99

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.